Appl. No. 10/608,731
Amdt. Dated Oct. 26, 2004
Reply to Office action of Sept. 2, 2004

Amendments to the Specification:

[0045] Another advantageous sensor chip configuration, illustrated in FIG. 6, consists of a tungsten thin film 28 deposited as the sensor element on an insulating A1N substrate 30. The tungsten conductor preferably traces a serpentine pattern on the substrate 30 for even heat distribution when a heating current is applied to it, and terminates at each end in a pair of spaced contact pads 32. Tungsten provides a high degree of thermal sensitivity, and can tolerate a wide temperature range when used in conjunction with an AlN substrate because of their closely matched temperature coefficients of expansion. The thin film tungsten layer is generally about 10-1000 microns thick. Such a temperature sensor is the subject of copending patent application Serial No. -10/608,737, filed on the same date as the present application in the name of James D. Parsons, one of the present inventors.